

Deposit gate oxide

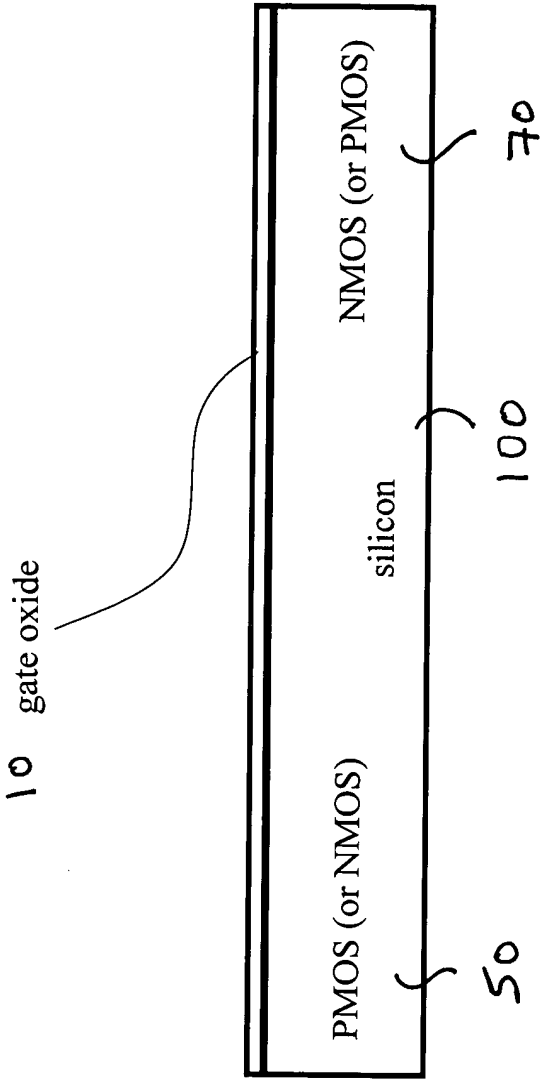


FIG. 1

Deposit thin layer of gate electrode material

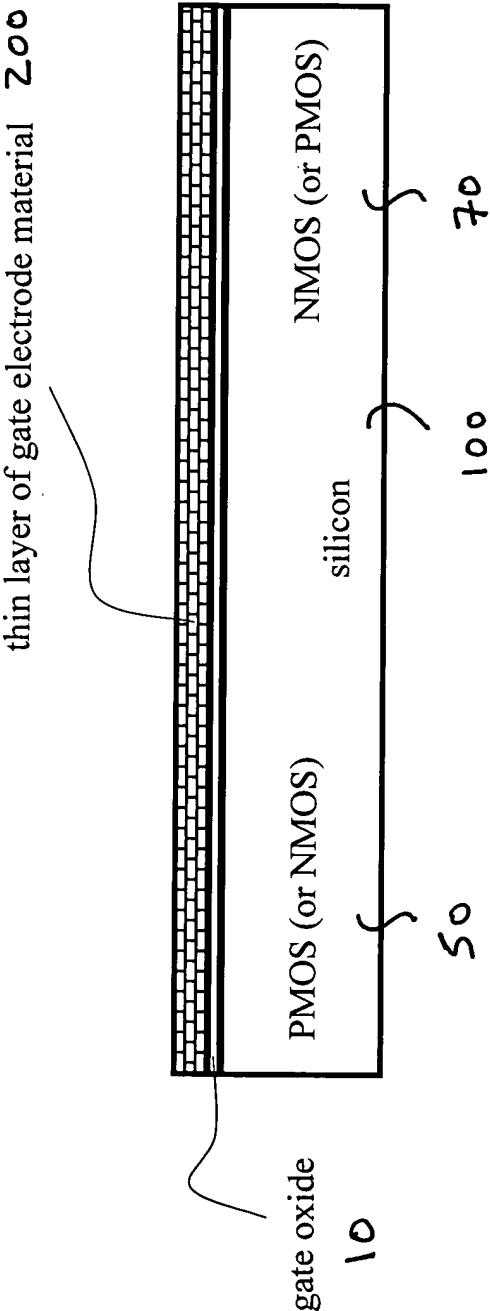


FIG. 2

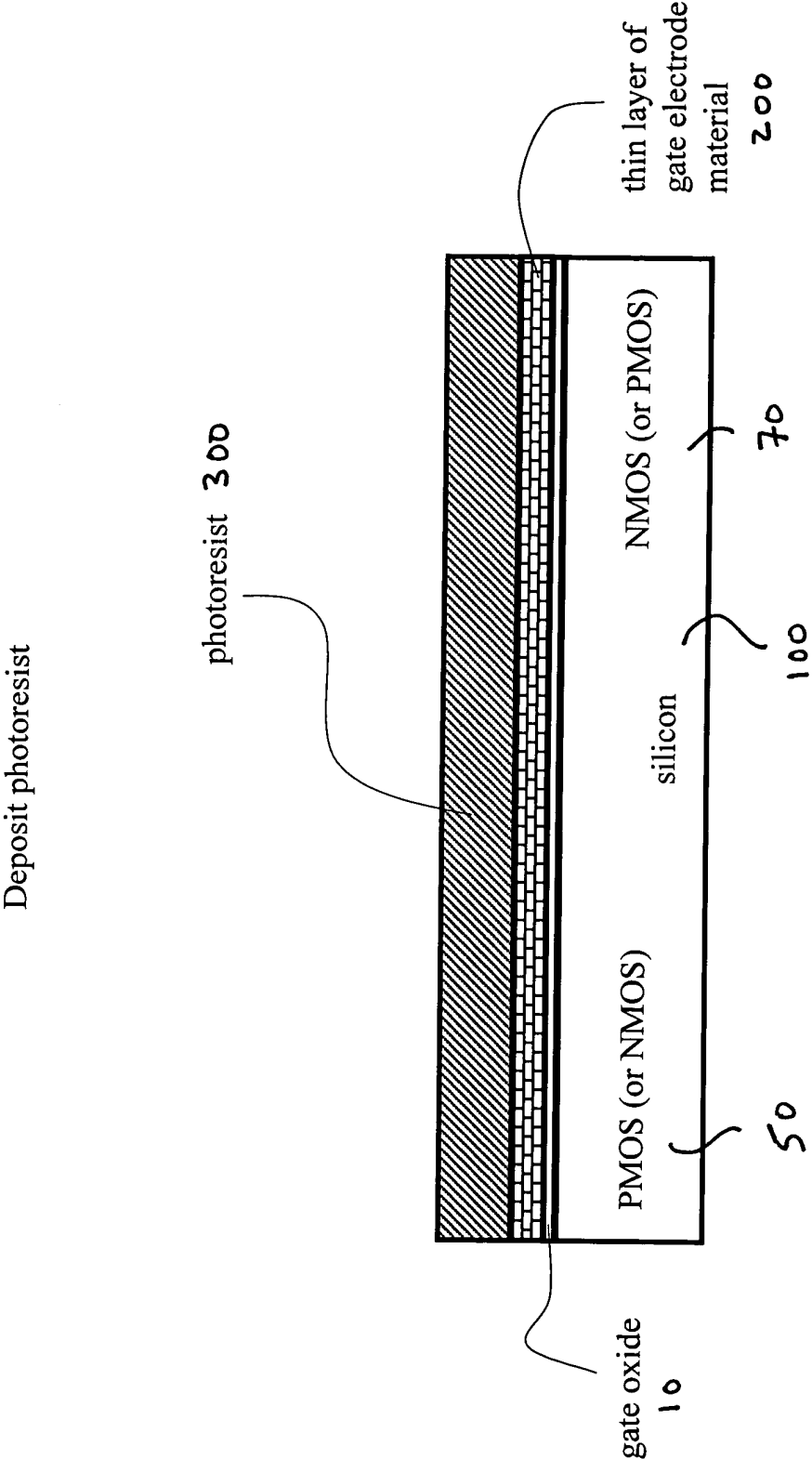


FIG. 3

Pattern and etch photoresist

patterned photoresist 300

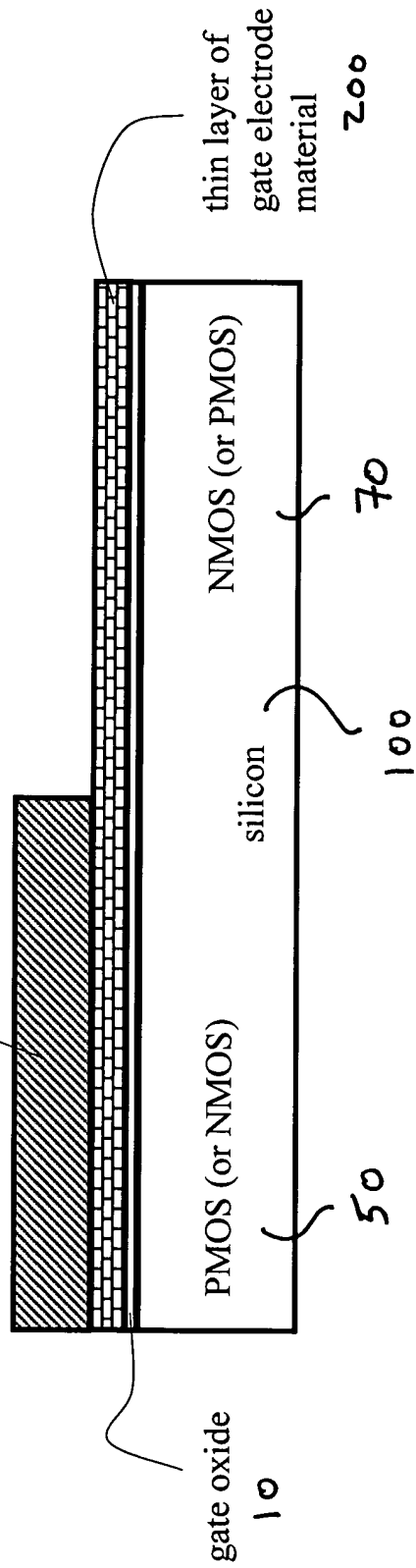


FIG. 4

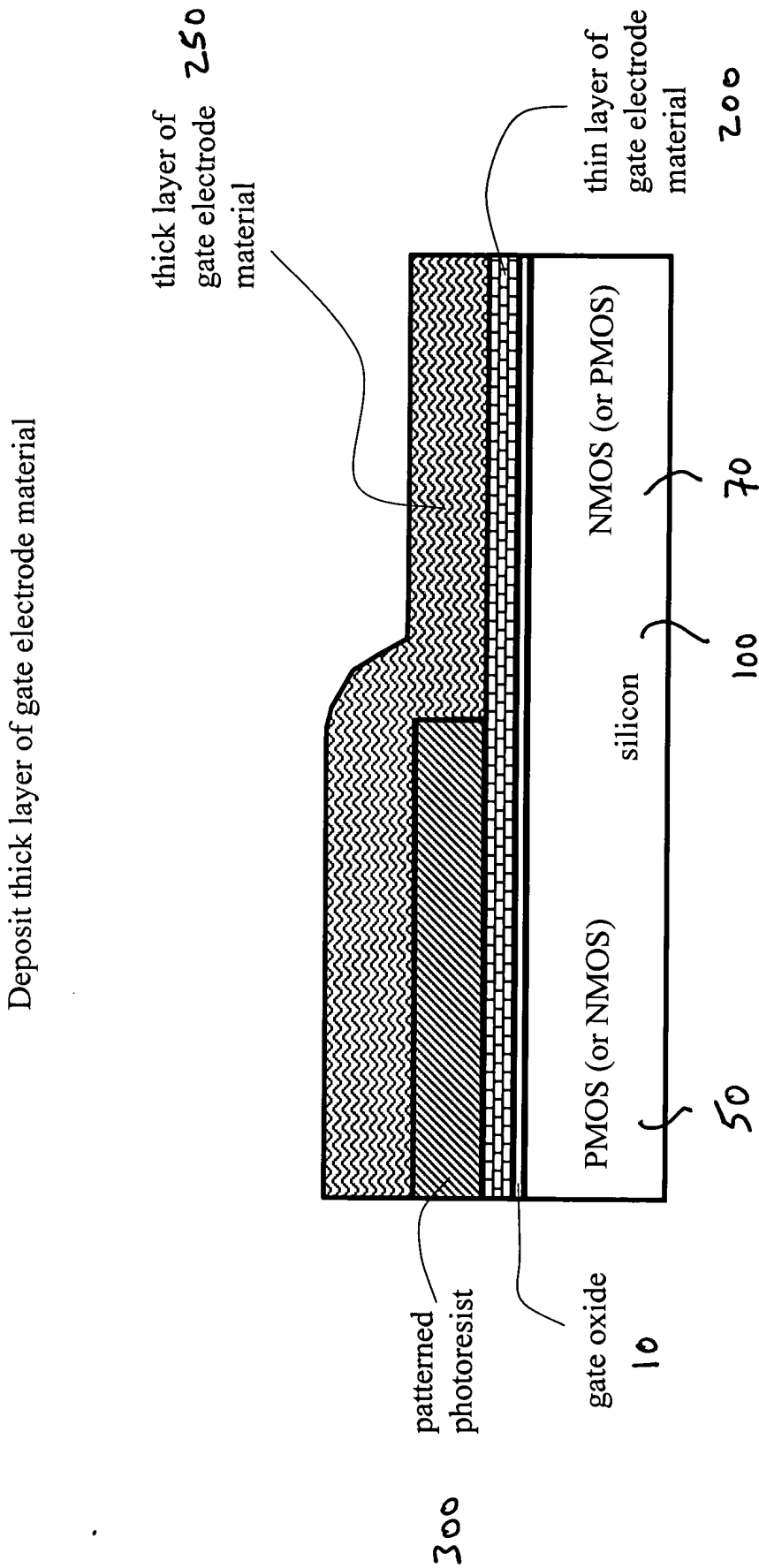


FIG. 5

Chemical mechanical polishing (CMP)

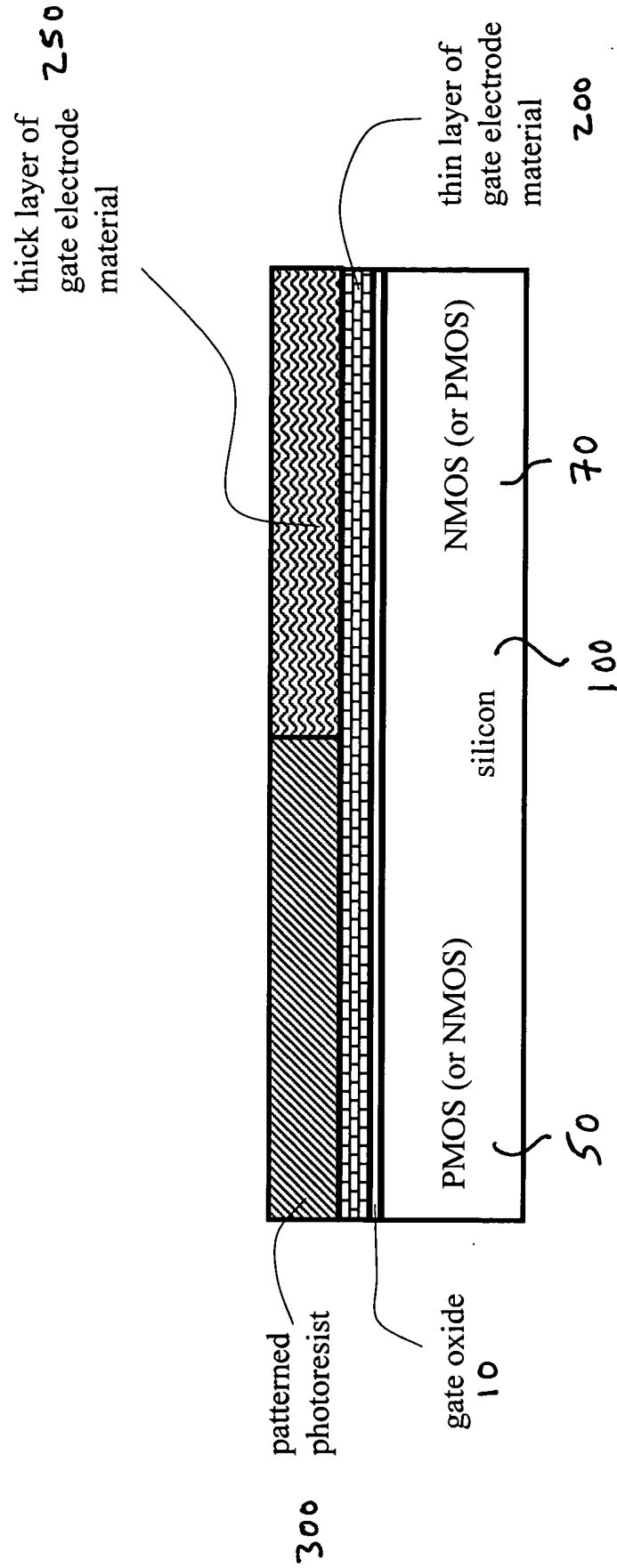


FIG. 6

Etch photoresist

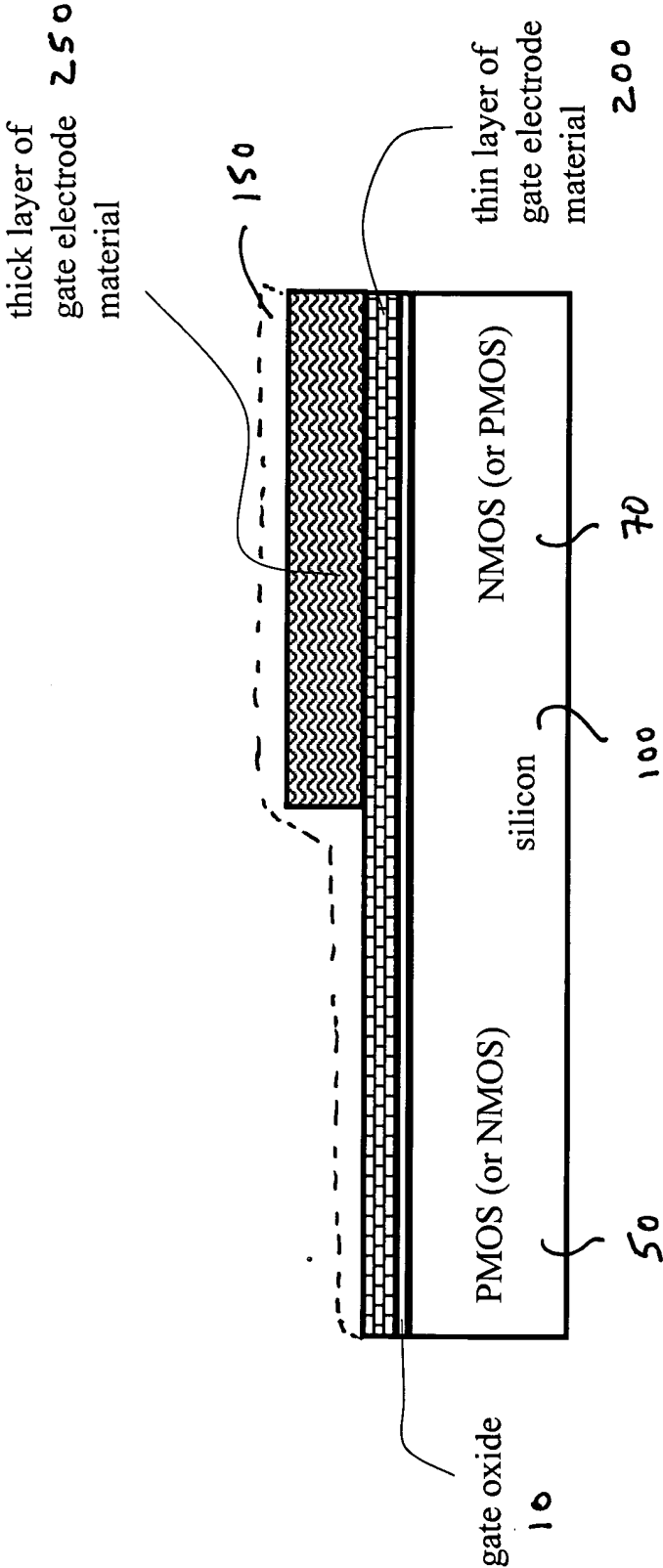


FIG. 7

Deposit thick conductor, such as poly-Si, W, Al, Ni, Ru, RuO<sub>2</sub>

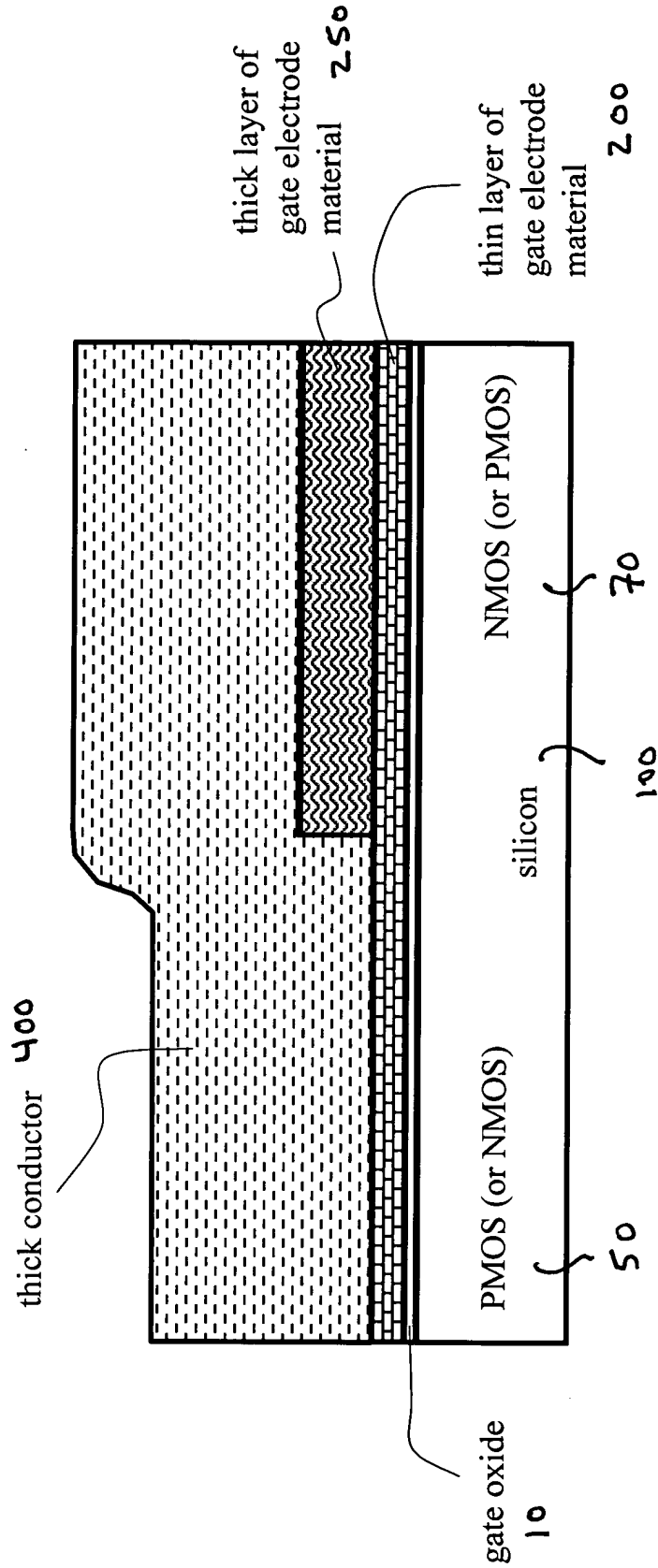


FIG. 8



Chemical mechanical polishing (CMP)

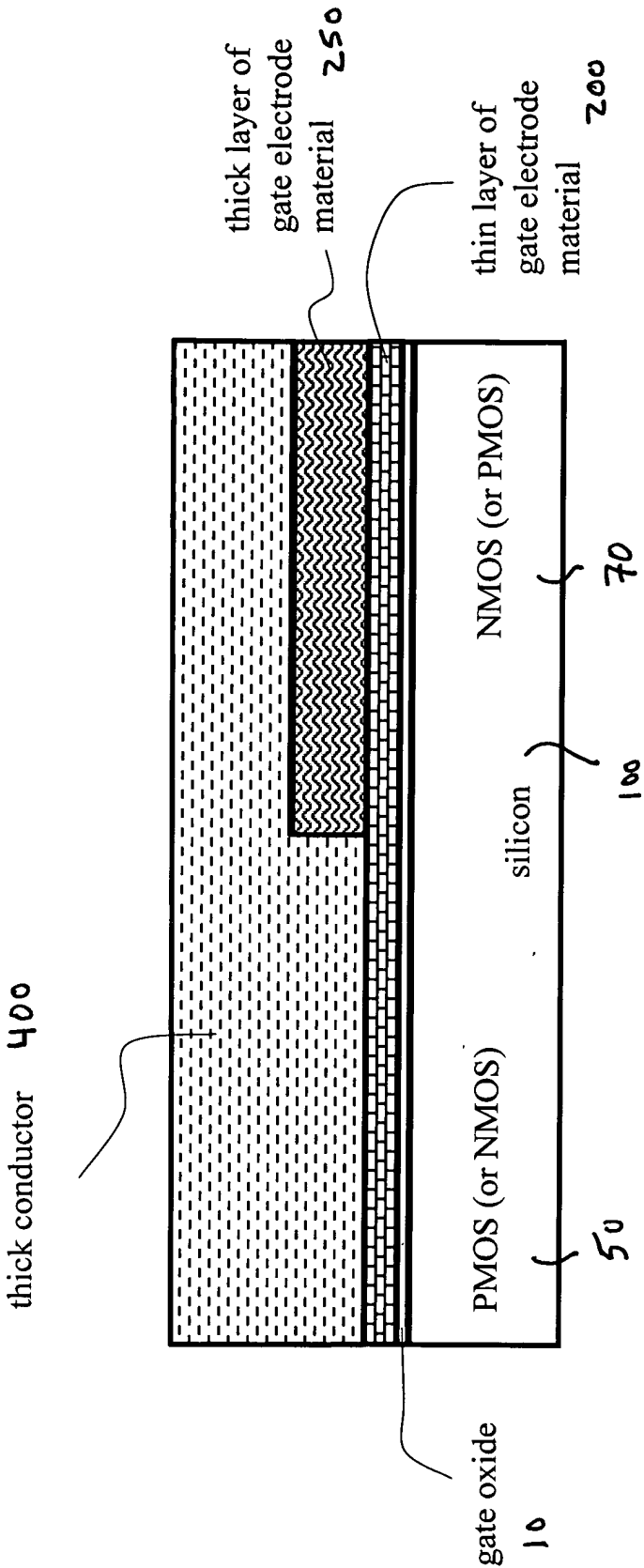


FIG. 9

Deposit gate oxide

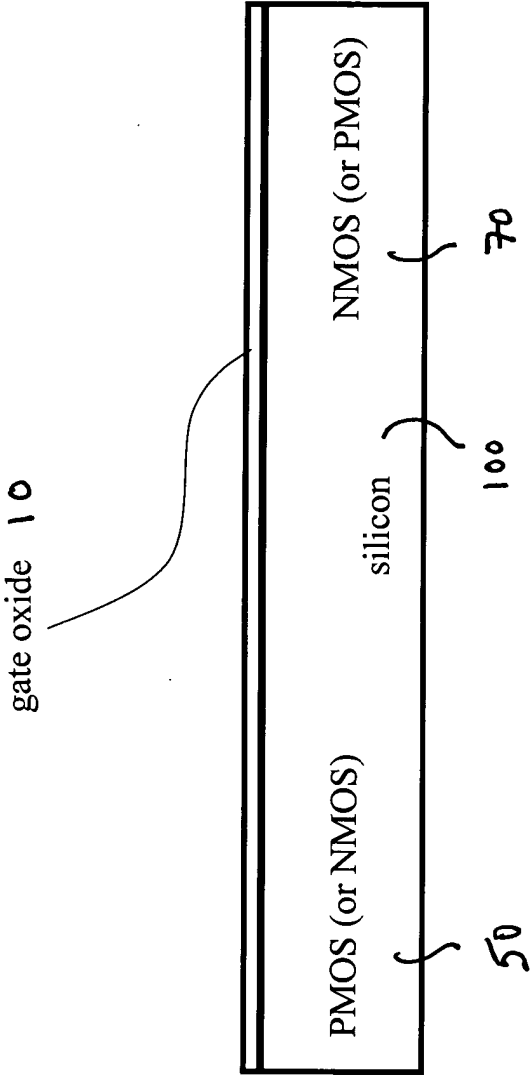


FIG. 10

Deposit thin layer of gate electrode material

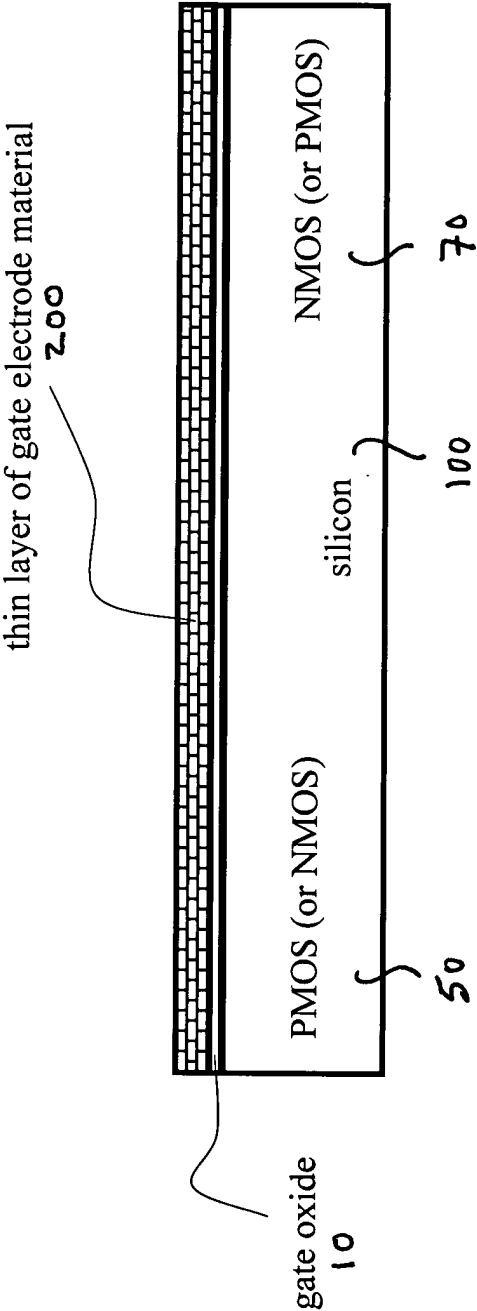


FIG. 11

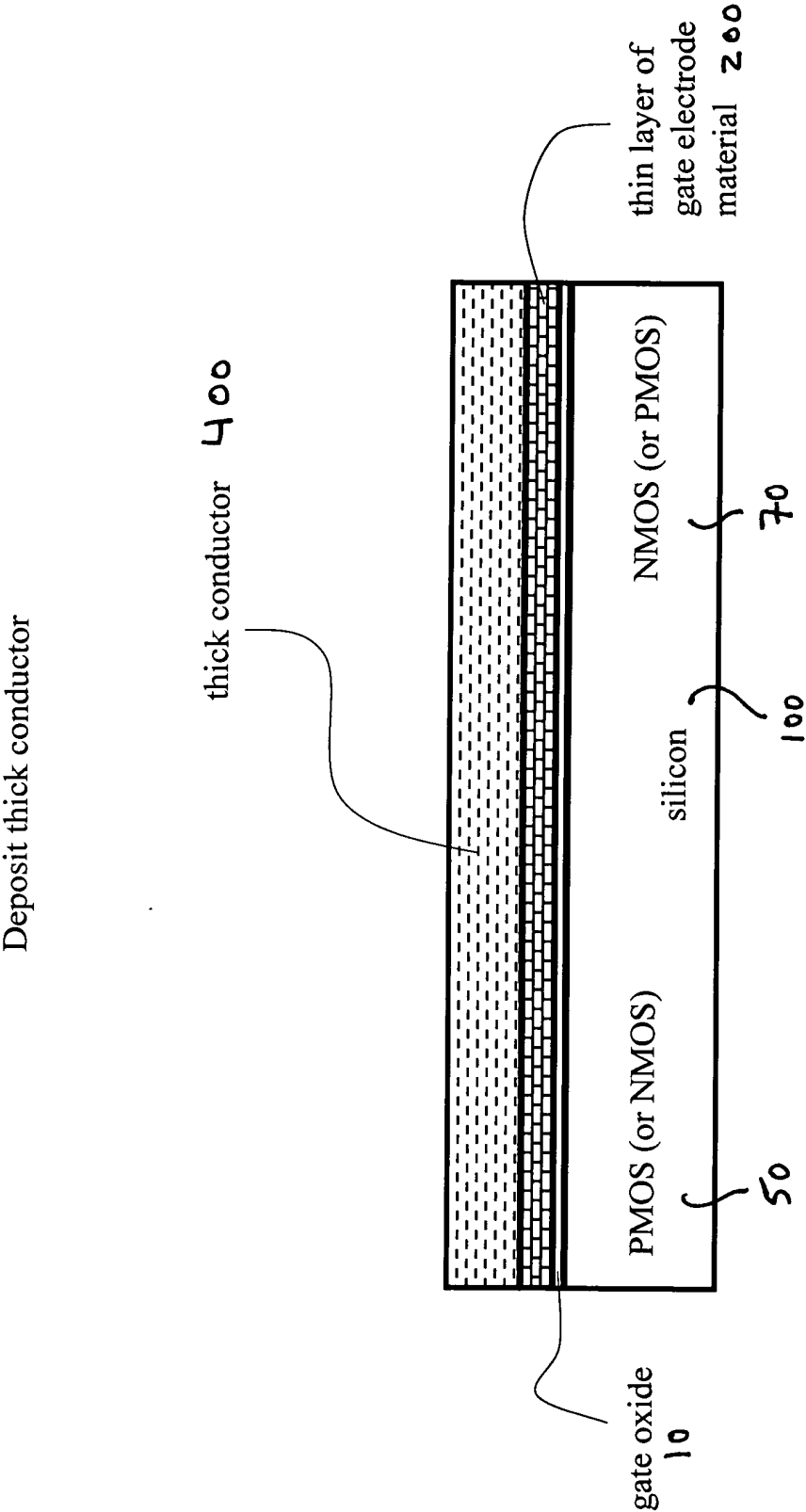


FIG. 12

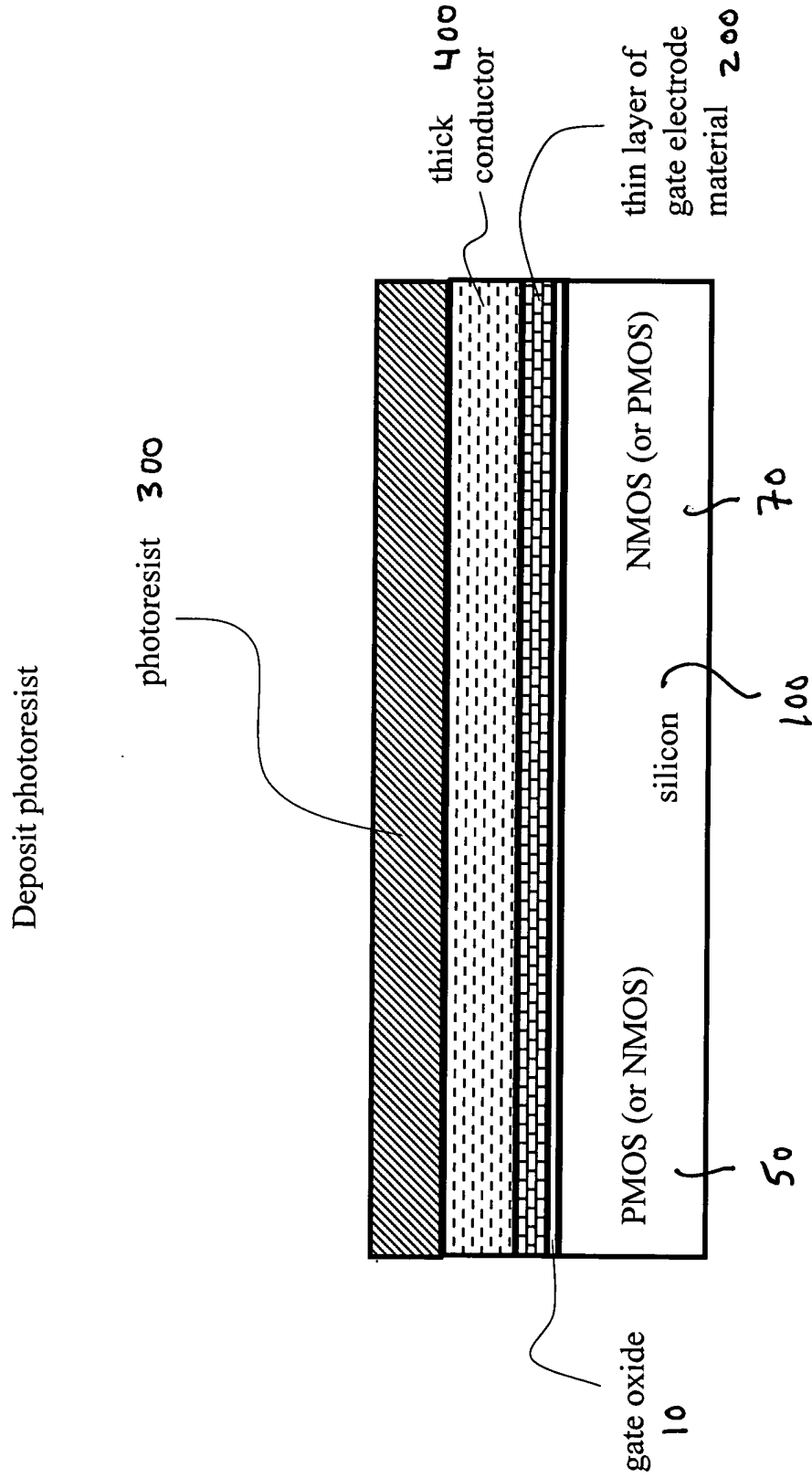


FIG. 13

Pattern and etch thick conductor

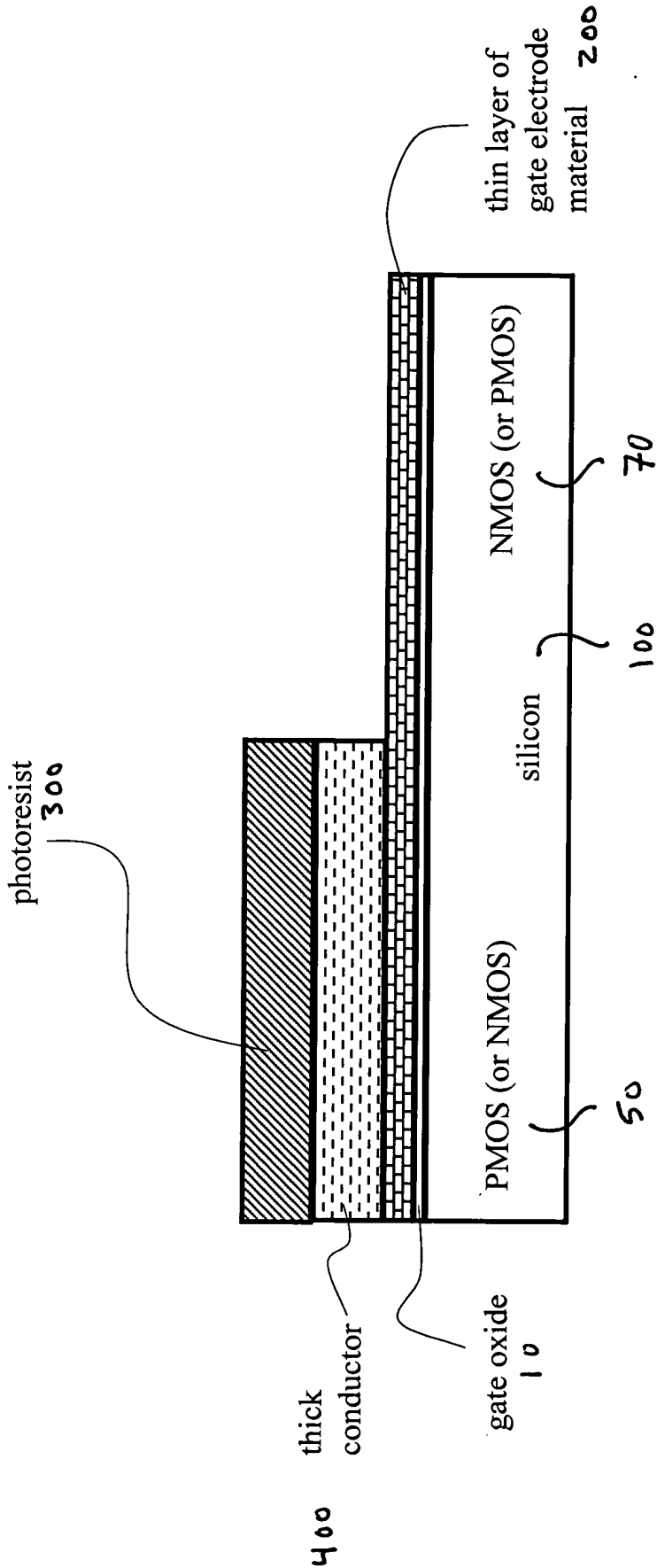


FIG. 14

Remove photoresist

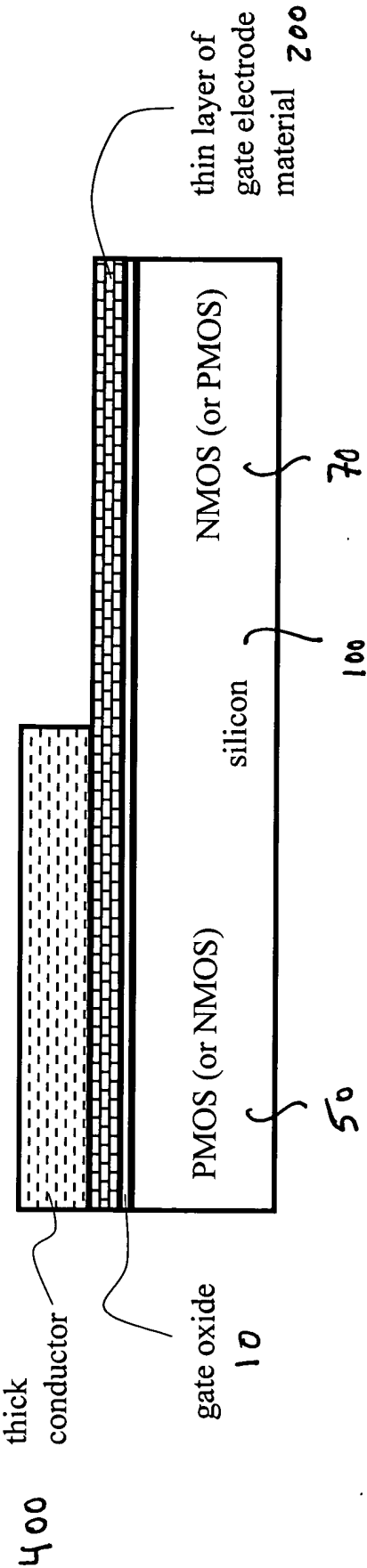


FIG. 15

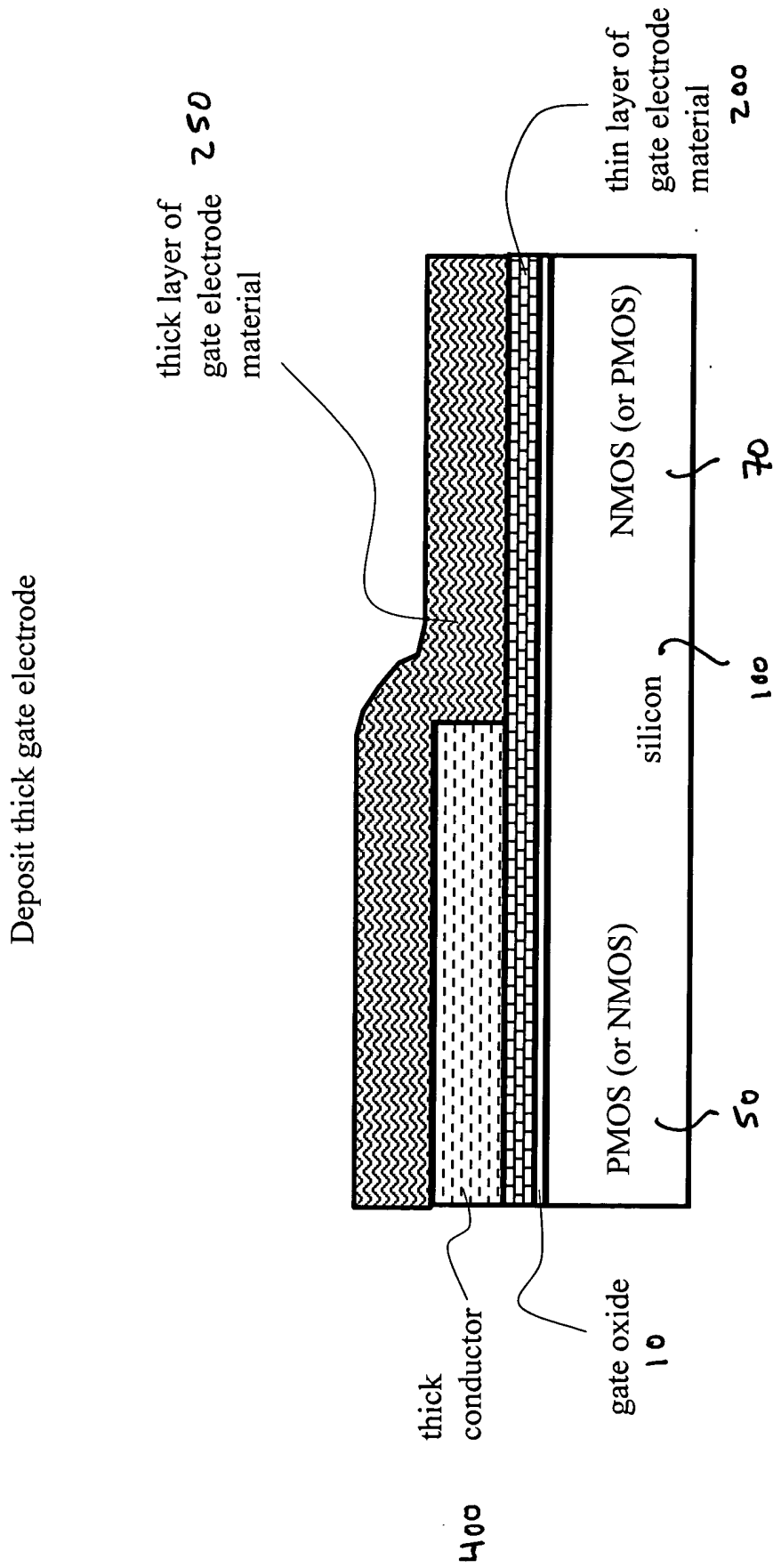


FIG. 16



Chemical mechanical polishing (CMP)

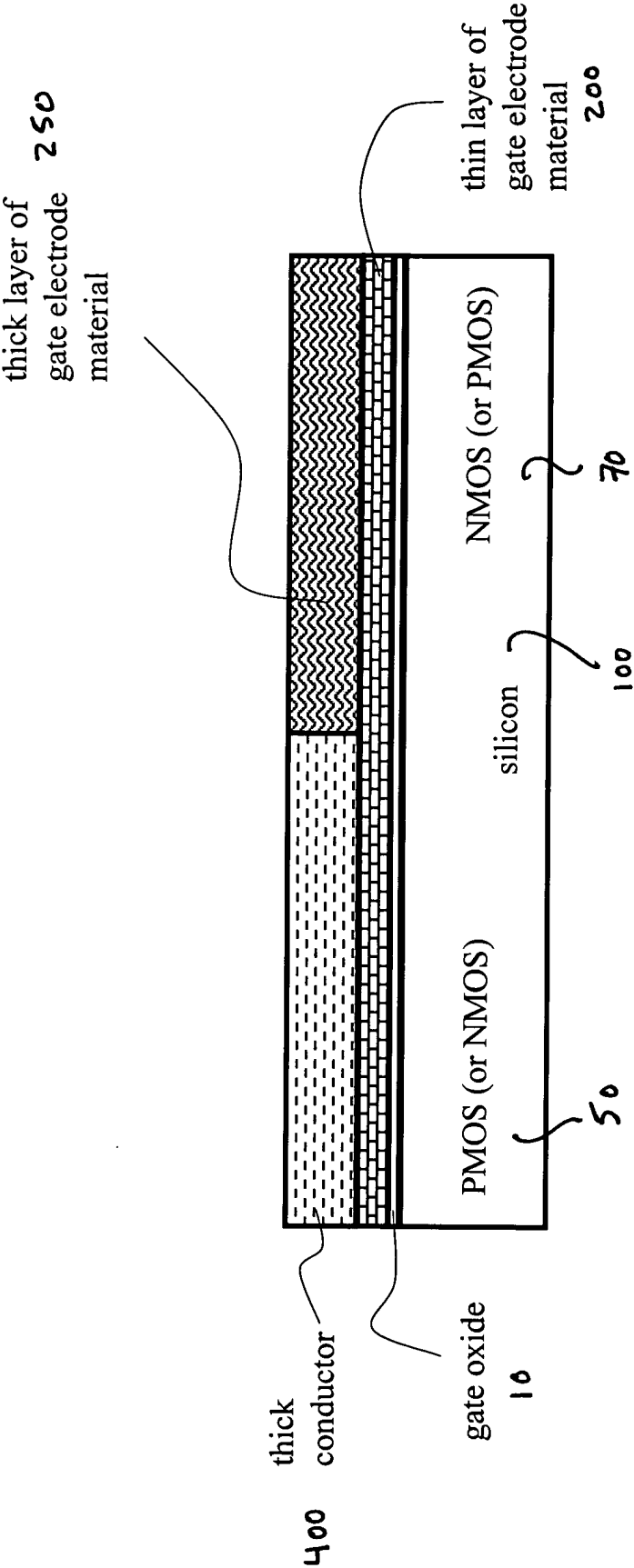


FIG. 17

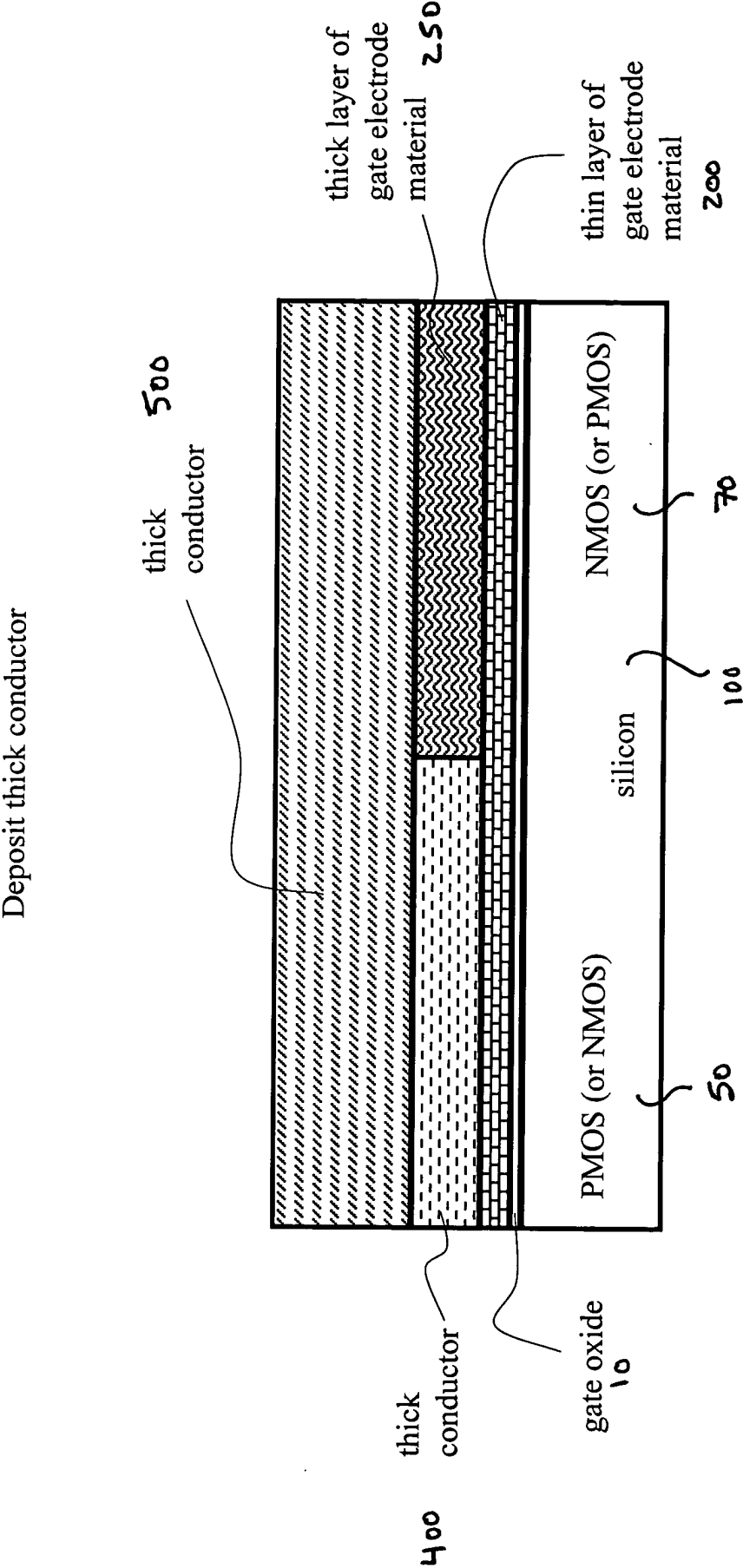


FIG. 18

Deposit gate oxide

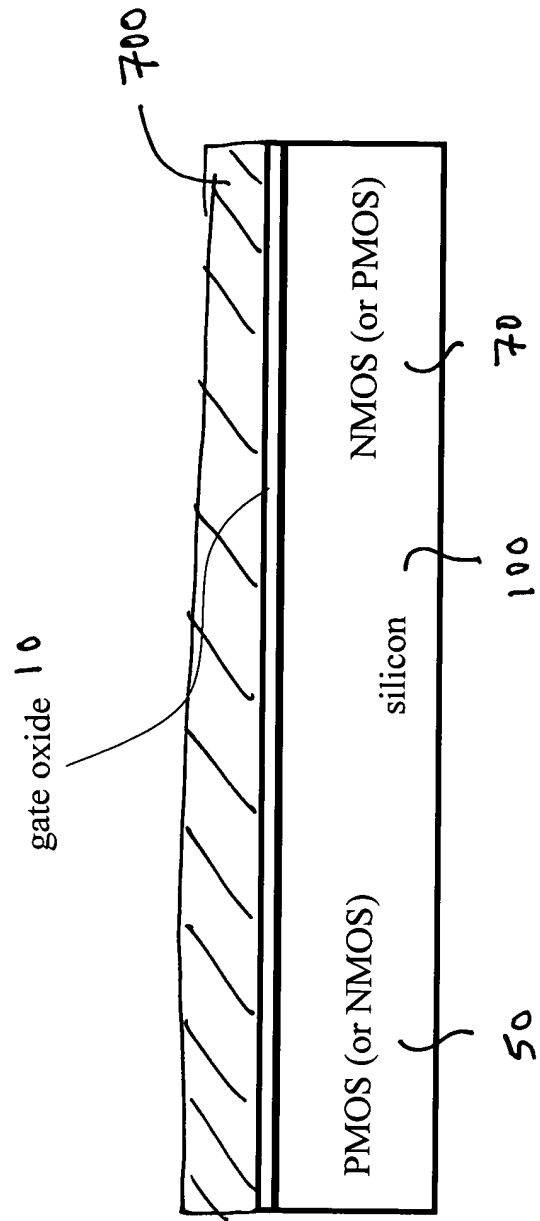


FIG. 19

Deposit gate oxide

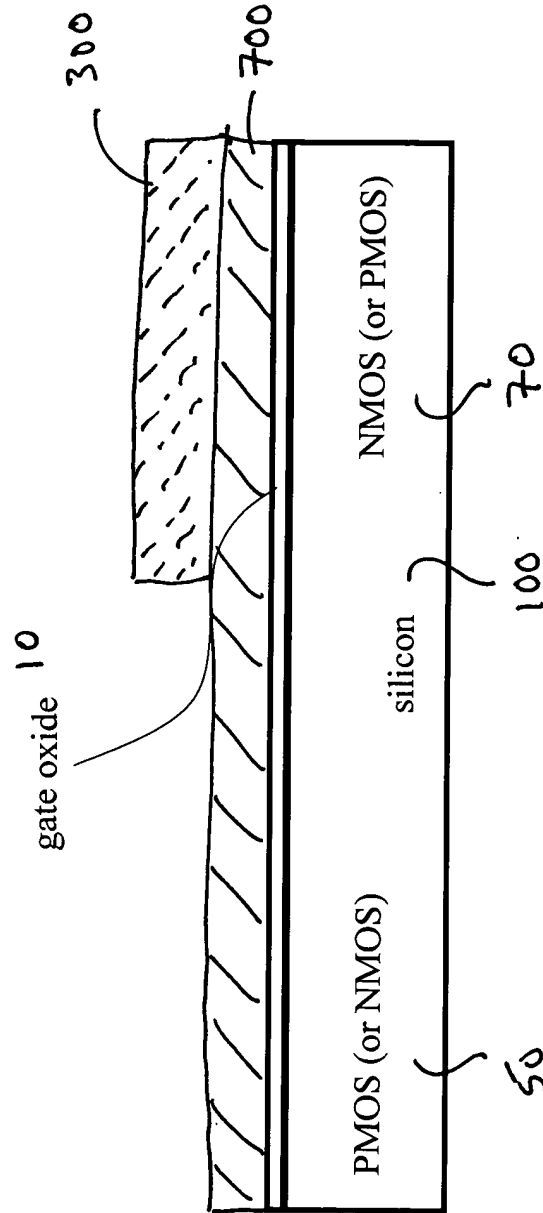


FIG. 20

Deposit gate oxide

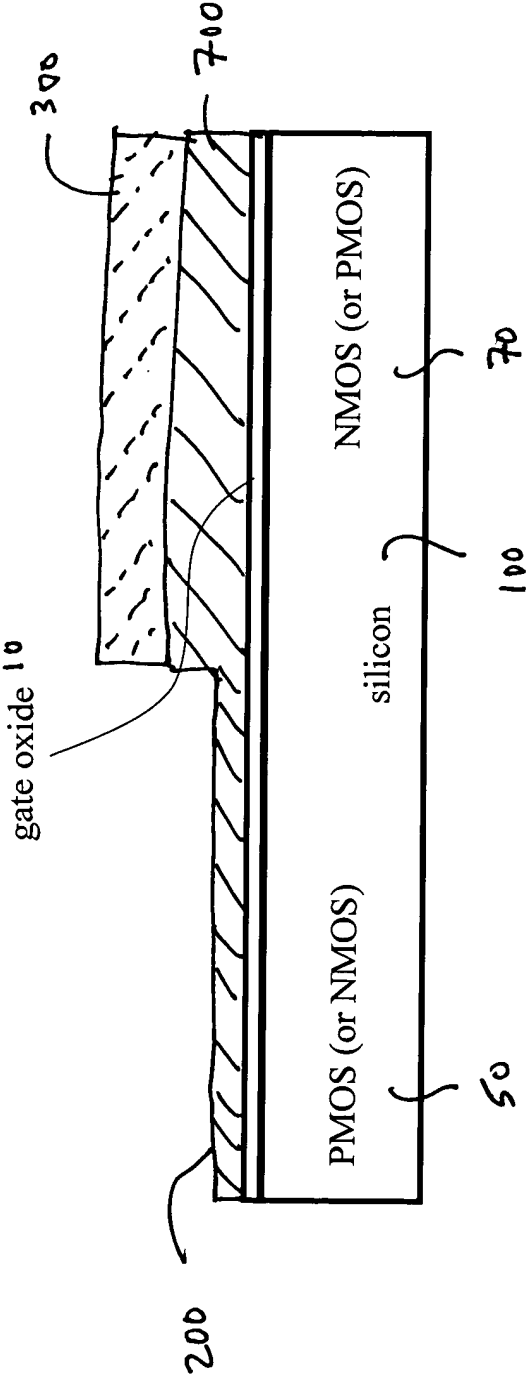


FIG. 1

Deposit gate oxide

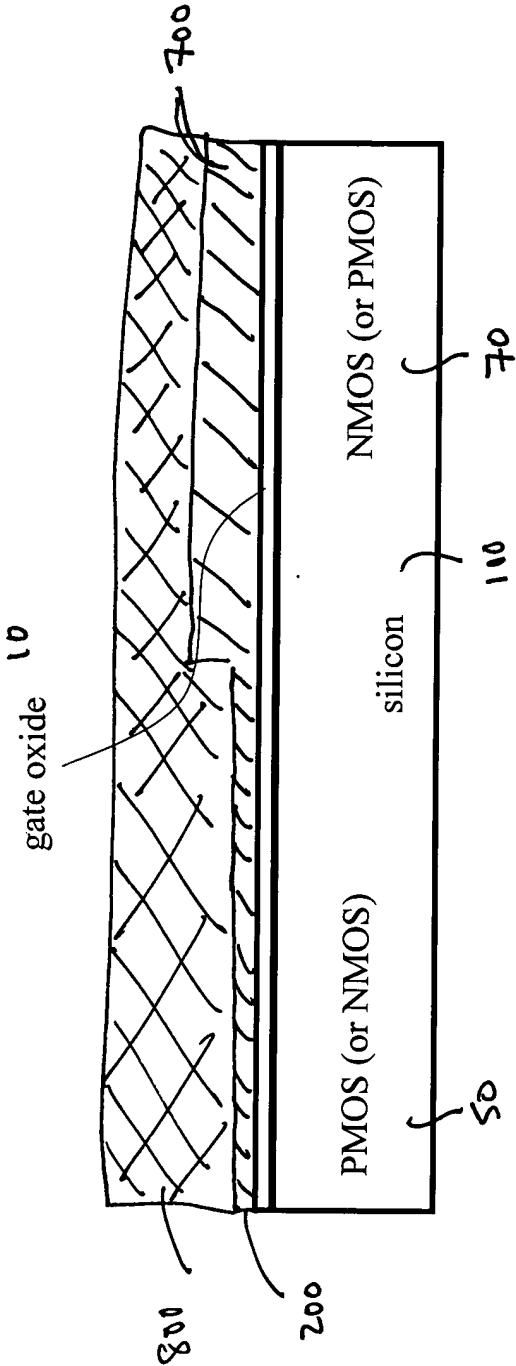


FIG. 12